

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



## FSL156MRBN Green-Mode Fairchild Power Switch (FPS™)

#### Features

- Advanced Soft Burst-Mode Operation for Low Standby Power and Low Audible Noise
- Random Frequency Fluctuation (RFF) for Low EMI
- Pulse-by-Pulse Current Limit
- Various Protection Functions: Overload Protection (OLP), Over-Voltage Protection (OVP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD) with Hysteresis, Output-Short Protection (OSP), and Under-Voltage Lockout (UVLO) with Hysteresis
- Low Operating Current (0.4mA) in Burst Mode
- Internal Startup Circuit
- Internal High-Voltage SenseFET: 650V
- Built-in Soft-Start: 15ms
- Auto-Restart Mode

#### Applications

 Power Supply for LCD Monitor, STB, and DVD Combination

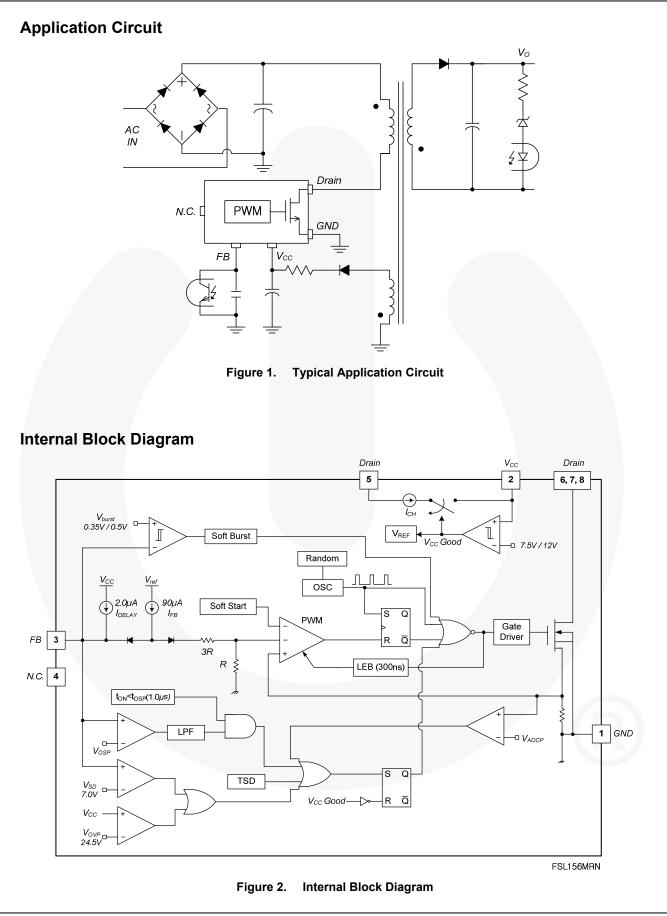
### Description

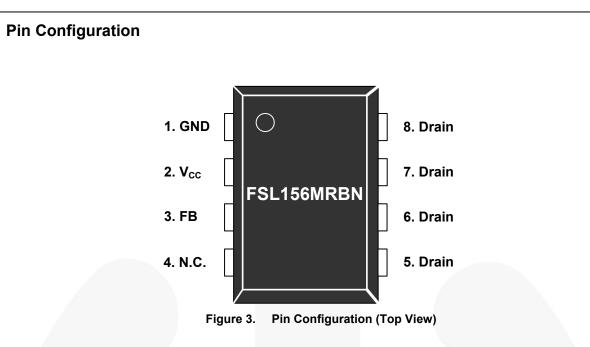
The FSL156MRBN is an integrated Pulse Width Modulation (PWM) controller and SenseFET specifically designed for offline Switch-Mode Power Supplies (SMPS) with minimal external components. The PWM controller includes an integrated fixed-frequency oscillator, Under-Voltage Lockout (UVLO), Leading-Edge Blanking (LEB), optimized gate driver, internal soft-start, temperature-compensated precise current sources for loop compensation, and self-protection circuitry. Compared with a discrete MOSFET and PWM controller solution, the FSL156MRBN series can reduce total cost, component count, size, and weight; while simultaneously increasing efficiency, productivity, and system reliability. This device provides a basic platform suited for cost-effective design of a flyback converter.

Ordering Information									
					Output Power Table <sup>(2)</sup>				
Part Number	Package	Operating Junction	Limit	ent R <sub>DS(ON)</sub> nit (Max.)			85-265V <sub>AC</sub>		Replaces
i an Number	i denage	Temperature			Adapter (4)	Open Frame <sup>(5)</sup>	Adapter (4)	Open Frame <sup>(5)</sup>	Device
FSL156MRBN	8-DIP	-40°C ~ +125°C	1.60A	2.2Ω	26W	40W	20W	30W	FSFM300N FSGM300
NI - 4					•	•			

#### Notes:

- 1. Lead-free package per JEDEC J-STD-020B.
- 2. The junction temperature can limit the maximum output power.
- 3.  $230V_{AC}$  or  $100/115V_{AC}$  with voltage doubler.
- 4. Typical continuous power in a non-ventilated enclosed adapter measured at 50°C ambient temperature.
- 5. Maximum practical continuous power in an open-frame design at 50°C ambient temperature.





### **Pin Definitions**

Pin #	Name	Description				
1	GND	Ground. This pin is the control ground and the SenseFET source.				
2	V <sub>CC</sub>	wer Supply. This pin is the positive supply input, which provides the internal operating rent for both startup and steady-state operation.				
3	FB	<b>Feedback</b> . This pin is internally connected to the inverting input of the PWM comparator. The collector of an opto-coupler is typically tied to this pin. For stable operation, a capacitor should be placed between this pin and GND. If the voltage of this pin reaches 7.0V, the overload protection triggers, which shuts down the FPS <sup>™</sup> .				
4	N.C.	No Connection				
5, 6, 7, 8	Drain	SenseFET Drain. High-voltage power SenseFET drain connection.				

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter		Min.	Max.	Unit
V <sub>DS</sub>	Drain Pin Voltage				650	V
Vcc	V <sub>CC</sub> Pin Voltage				26	V
V <sub>FB</sub>	Feedback Pin Voltage			-0.3	10.0	V
I <sub>DM</sub>	Drain Current Pulsed				4	А
	Osetienen Ositekies		T <sub>C</sub> =25°C		1.90	А
I <sub>DS</sub>	Continuous Switching Drain Current <sup>(6)</sup> T <sub>C</sub> =100°C				1.27	А
E <sub>AS</sub>	Single Pulsed Avalance	he Energy <sup>(7)</sup>			190	mJ
PD	Total Power Dissipation	on (T <sub>C</sub> =25°C) <sup>(8)</sup>			1.5	W
-	Maximum Junction Te	mperature			150	°C
TJ	Operating Junction Te	-40	+125	°C		
T <sub>STG</sub>	Storage Temperature	-55	+150	°C		
FOD	Electrostatic	I, JESD22-A114		5		
ESD	Discharge Capability Charged Device Model, JESD22-C101				2	kV

Notes:

6. Repetitive peak switching current when the inductive load is assumed: Limited by maximum duty (D<sub>MAX</sub>=0.73) and junction temperature (see Figure 4).

- 7. L=45mH, starting TJ=25°C.
- 8. Infinite cooling condition (refer to the SEMI G30-88).
- 9. Although this parameter guarantees IC operation, it does not guarantee all electrical characteristics.

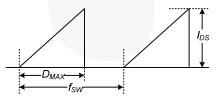


Figure 4. Repetitive Peak Switching Current

#### **Thermal Impedance**

T<sub>A</sub>=25°C unless otherwise specified.

Symbol	Parameter		Unit
θ <sub>JA</sub>	Junction-to-Ambient Thermal Impedance <sup>(10)</sup>		°C/W
$\Psi_{JL}$	Junction-to-Lead Thermal Impedance <sup>(11)</sup>	11	°C/W

#### Notes:

10. JEDEC recommended environment, JESD51-2 and test board, JESD51-10 with minimum land pattern.

11. Measured on the SOURCE pin #7, close to the plastic interface.

### **Electrical Characteristics**

 $T_J$  = 25°C unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
SenseFET	Section						1
BV <sub>DSS</sub>	Drain-Source B	reakdown Voltage	$V_{CC} = 0V, I_D = 250\mu A$	650			V
I <sub>DSS</sub>	Zero-Gate-Volta	age Drain Current	V <sub>DS</sub> = 650V, T <sub>A</sub> = 25°C			250	μA
R <sub>DS(ON)</sub>	Drain-Source O	n-State Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =1A		1.8	2.2	Ω
CISS	Input Capacitan	ice <sup>(12)</sup>	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f=1MHz		515		pF
Coss	Output Capacita	ance <sup>(12)</sup>	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f=1MHz		75		pF
tr	Rise Time		$V_{DS}$ = 325V, $I_{D}$ = 4A, $R_{G}$ =25 $\Omega$		26		ns
t <sub>f</sub>	Fall Time		$V_{DS}$ = 325V, $I_{D}$ = 4A, $R_{G}$ =25 $\Omega$		25		ns
t <sub>d(on)</sub>	Turn-On Delay		$V_{DS}$ = 325V, $I_{D}$ = 4A, $R_{G}$ =25 $\Omega$		14		ns
$t_{d(off)}$	Turn-Off Delay		$V_{DS}$ = 325V, $I_{D}$ = 4A, $R_{G}$ = 25 $\Omega$		32		ns
Control Se	ction				•		
f <sub>S</sub>	Switching Frequ	uency <sup>(12)</sup>	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 4V	61	67	73	kHz
$\Delta f_S$	Switching Frequ	uency Variation <sup>(12)</sup>	−25°C < T <sub>J</sub> < 125°C		±5	±10	%
D <sub>MAX</sub>	Maximum Duty	Ratio	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 4V	61	67	73	%
D <sub>MIN</sub>	Minimum Duty I	Ratio	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 0V			0	%
I <sub>FB</sub>	Feedback Sour	ce Current	V <sub>FB</sub> = 0	65	90	115	μA
V <sub>START</sub>	UVLO Threshold Voltage		V <sub>FB</sub> = 0V, V <sub>CC</sub> Sweep	11	12	13	V
VSTOP			After Turn-On, V <sub>FB</sub> = 0V	7.0	7.5	8.0	V
t <sub>ss</sub>	Internal Soft-Sta	art Time	V <sub>STR</sub> = 40V, V <sub>CC</sub> Sweep		15		ms
V <sub>RECOMM</sub>	Recommended	V <sub>CC</sub> Range		13		23	V
Burst-Mode	e Section						
V <sub>BURH</sub>				0.45	0.50	0.55	V
VBURL	Burst-Mode Vol	tage	V <sub>CC</sub> = 14V, V <sub>FB</sub> Sweep	0.30	0.35	0.40	V
V <sub>HYS</sub>					150		mV
Protection	Section						
I <sub>LIM</sub>	Peak Drain Cur	rent Limit	di/dt = 300mA/µs	1.45	1.60	1.75	А
V <sub>SD</sub>	Shutdown Feed	Iback Voltage	V <sub>CC</sub> = 14V, V <sub>FB</sub> Sweep	6.45	7.00	7.55	V
IDELAY	Shutdown Dela	y Current	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 4V	1.2	2.0	2.8	μA
t <sub>LEB</sub>	Leading-Edge E	Blanking Time <sup>(12,14)</sup>			300		ns
V <sub>OVP</sub>	Over-Voltage P	rotection	V <sub>CC</sub> Sweep	23.0	24.5	26.0	V
t <sub>OSP</sub>		Threshold Time	OSP Triggered when	0.7	1.0	1.3	μs
V <sub>OSP</sub>	Output-Short Protection <sup>(12)</sup>	Threshold V <sub>FB</sub>	t <sub>ON</sub> <t<sub>OSP &amp; V<sub>FB</sub>&gt;V<sub>OSP</sub></t<sub>	1.8	2.0	2.2	V
tosp_fb		V <sub>FB</sub> Blanking Time	(Lasts Longer than t <sub>OSP_FB</sub> )	2.0	2.5	3.0	μs
TSD	TIME		Shutdown Temperature	125	135	145	°C
T <sub>HYS</sub>	I hermal Shutdo	own Temperature <sup>(12)</sup>	Hysteresis		60		°C

FSL156MRBN — Green-Mode Fairchild Power Switch (FPS™)

Continued on the following page...

### Electrical Characteristics (Continued)

 $T_{\rm J}$  = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
Total Devic	Fotal Device Section						
I <sub>OP</sub>	Operating Supply Current, (Control Part in Burst Mode)	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 0V	0.3	0.4	0.5	mA	
I <sub>OPS</sub>	Operating Switching Current, (Control Part and SenseFET Part)	V <sub>CC</sub> = 14V, V <sub>FB</sub> = 2V	1.1	1.5	1.9	mA	
I <sub>START</sub>	Start Current	$V_{CC}$ =11V (Before $V_{CC}$ Reaches $V_{START}$ )	85	120	155	μA	
I <sub>CH</sub>	Startup Charging Current	$V_{CC} = V_{FB} = 0V$ , $V_{STR} = 40V$	0.7	1.0	1.3	mA	
V <sub>STR</sub>	Minimum V <sub>STR</sub> Supply Voltage	$V_{CC} = V_{FB} = 0V, V_{STR}$ Sweep		26		V	

Notes:

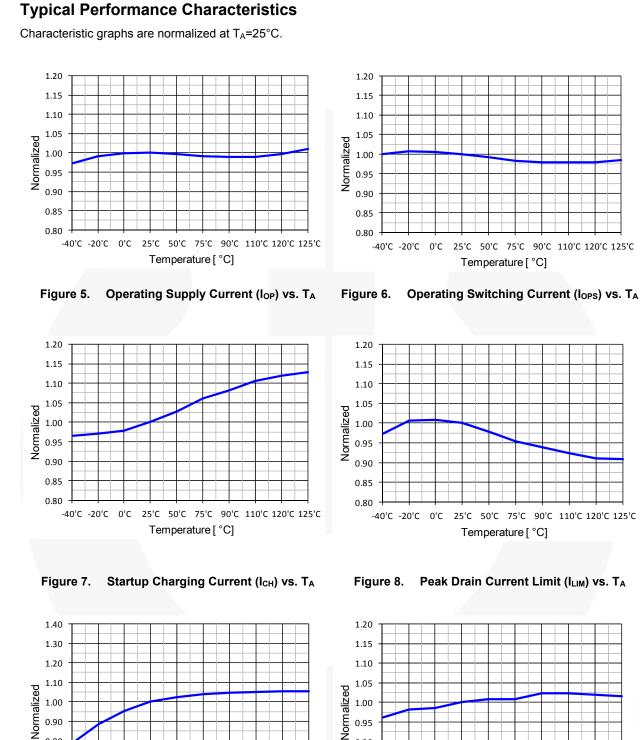
12. Although these parameters are guaranteed, they are not 100% tested in production.

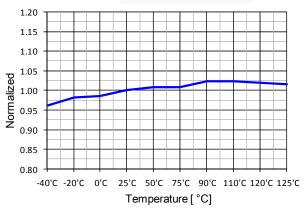
13. Average value.

14. t<sub>LEB</sub> includes gate turn-on time.

### Comparison of FSGM300N and FSL156MRBN

Function	FSGM300N	FSL156MRBN	Advantages of FSL156MRBN
Operating Current	1.5mA	0.4mA	Very low standby power
Power Balance	Long t <sub>CLD</sub>	Very Short $t_{CLD}$	The difference of input power between the low and high input voltage is quite small.







-40'C -20'C 0'C 25'C 50'C 75'C 90'C 110'C 120'C 125'C

Temperature [ °C]

Feedback Source Current (IFB) vs. TA

1.00

0.90

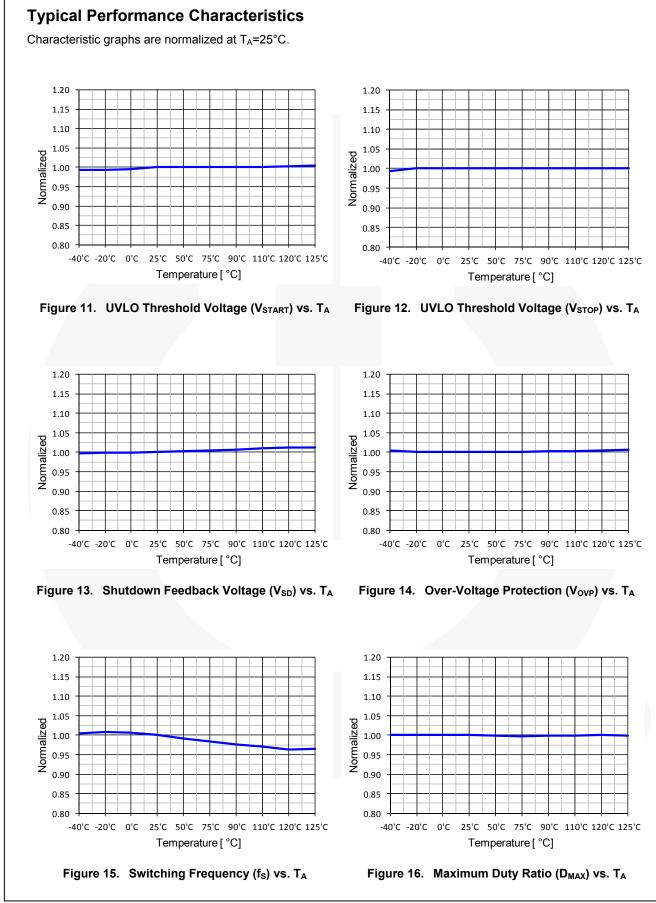
0.80

0.70

0.60

Figure 9.

FSL156MRBN — Green-Mode Fairchild Power Switch (FPS™)



### **Functional Description**

**1. Startup:** At startup, an internal high-voltage current source supplies the internal bias and charges the external capacitor ( $C_{Vcc}$ ) connected to the  $V_{CC}$  pin, as illustrated in Figure 17. When  $V_{CC}$  reaches 12V, the FSL156MRBN begins switching and the internal high-voltage current source is disabled. Normal switching operation continues and the power is supplied from the auxiliary transformer winding unless  $V_{CC}$  goes below the stop voltage of 7.5V.

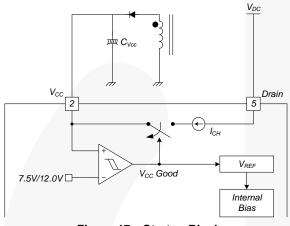


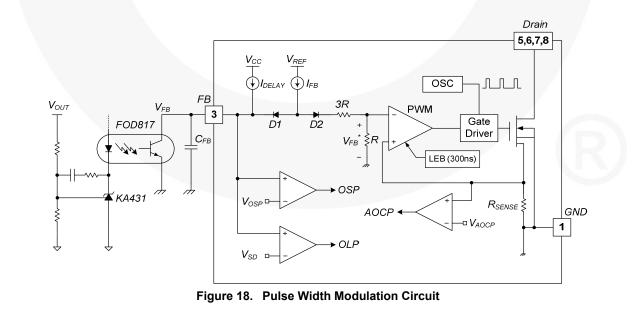
Figure 17. Startup Block

**2. Soft-Start**: The internal soft-start circuit increases PWM comparator inverting input voltage, together with the SenseFET current, slowly after startup. The typical soft-start time is 15ms. The pulse width to the power switching device is progressively increased to establish the correct working conditions for the transformers, inductors, and capacitors. The voltage on the output capacitors is progressively increased to smoothly establish the required output voltage. This helps prevent transformer saturation and reduces stress on the secondary diode during startup.

**3. Feedback Control**: This device employs Current-Mode control, as shown in Figure 18. An opto-coupler (such as the FOD817) and shunt regulator (such as the KA431) are typically used to implement the feedback network. Comparing the feedback voltage with the voltage across the  $R_{SENSE}$  resistor makes it possible to control the switching duty cycle. When the reference pin voltage of the shunt regulator exceeds the internal reference voltage of 2.5V, the opto-coupler LED current increases, pulling down the feedback voltage and reducing drain current. This typically occurs when the input voltage is increased or the output load is decreased.

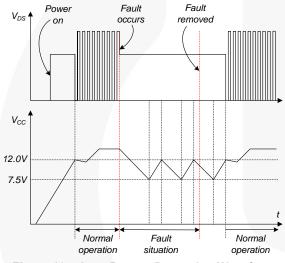
**3.1 Pulse-by-Pulse Current Limit**: Because Current-Mode control is employed, the peak current through the SenseFET is limited by the inverting input of PWM comparator (V<sub>FB</sub>\*), as shown in Figure 18. Assuming that the 90µA current source flows only through the internal resistor (3R + R =25kΩ), the cathode voltage of diode D2 is about 2.8V. Since D1 is blocked when the feedback voltage (V<sub>FB</sub>) exceeds 2.8V, the maximum voltage of the cathode of D2 is clamped at this voltage. Therefore, the peak value of the current through the SenseFET is limited.

**3.2 Leading-Edge Blanking (LEB)**: At the instant the internal SenseFET is turned on, a high-current spike usually occurs through the SenseFET, caused by primary-side capacitance and secondary-side rectifier reverse recovery. Excessive voltage across the R<sub>SENSE</sub> resistor leads to incorrect feedback operation in the Current-Mode PWM control. To counter this effect, the leading-edge blanking (LEB) circuit inhibits the PWM comparator for t<sub>LEB</sub> (300ns) after the SenseFET is turned on.



FSL156MRBN — Green-Mode Fairchild Power Switch (FPS™)

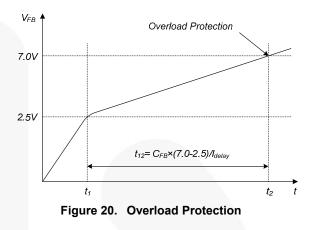
4. Protection Circuits: The FSL156MRBN has several self-protective functions, such as Overload Protection (OLP), Abnormal Over-Current Protection (AOCP), Output-Short Protection (OSP), Over-Voltage Protection (OVP), and Thermal Shutdown (TSD). All the protections are implemented as auto-restart. Once the fault condition is detected, switching is terminated and the SenseFET remains off. This causes  $V_{\text{CC}}$  to fall. When V<sub>CC</sub> falls to the Under-Voltage Lockout (UVLO) stop voltage of 7.5V, the protection is reset and the startup circuit charges the  $V_{CC}$  capacitor. When  $V_{CC}$ reaches the start voltage of 12.0V, normal operation resumes. If the fault condition is not removed, the SenseFET remains off and V<sub>CC</sub> drops to stop voltage again. In this manner, the auto-restart can alternately enable and disable the switching of the power SenseFET until the fault condition is eliminated. Because these protection circuits are fully integrated into the IC without external components, reliability is improved without increasing cost.



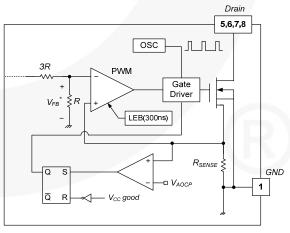


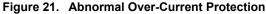
4.1 Overload Protection (OLP): Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the SMPS. However, even when the SMPS is in normal operation, the overload protection circuit can be triggered during the load transition. To avoid this undesired operation, the overload protection circuit is designed to trigger only after a specified time to determine whether it is a transient situation or a true overload situation. Because of the pulse-by-pulse current-limit capability, the maximum peak current through the SenseFET is limited and, therefore, the maximum input power is restricted with a given input voltage. If the output consumes more than this maximum power, the output voltage ( $V_{OUT}$ ) decreases below the set voltage. This reduces the current through the opto-coupler LED, which also reduces the opto-coupler transistor current, increasing the feedback voltage (VFB). If VFB exceeds 2.5V, D1 is blocked and the 2.0µA current source starts to charge

 $C_{FB}$  slowly up. In this condition,  $V_{FB}$  continues increasing until it reaches 7.0V, when the switching operation is terminated, as shown in Figure 20. The delay for shutdown is the time required to charge  $C_{FB}$  from 2.5V to 7.0V with 2.0µA. A 25 ~ 50ms delay is typical for most applications. This protection is implemented in Auto-Restart Mode.



4.2 Abnormal Over-Current Protection (AOCP): When the secondary rectifier diodes or the transformer pins are shorted, a steep current with extremely high di/dt can flow through the SenseFET during the minimum turn-on time. Even though the FSL156MRBN has overload protection, it is not enough to protect in that abnormal case due to the severe current stress imposed on the SenseFET until OLP is triggered. The internal AOCP circuit is shown in Figure 21. When the gate turn-on signal is applied to the power SenseFET, the AOCP block is enabled and monitors the current through the sensing resistor. The voltage across the resistor is compared with a preset AOCP level. If the sensing resistor voltage is greater than the AOCP level, the set signal is applied to the S-R latch, resulting in the shutdown of the SMPS.





**4.3. Output-Short Protection (OSP)**: If the output is shorted, steep current with extremely high di/dt can flow through the SenseFET during the minimum turnon time. Such a steep current brings high-voltage stress on the drain of the SenseFET when turned off. To protect the device from this abnormal condition, OSP is included. It is comprised of detecting V<sub>FB</sub> and SenseFET turn-on time. When the V<sub>FB</sub> is higher than 2.0V and the SenseFET turn-on time is lower than 1.0µs, this condition is recognized as an abnormal error and PWM switching shuts down until V<sub>CC</sub> reaches V<sub>START</sub> again. An abnormal condition output short is shown in Figure 22.

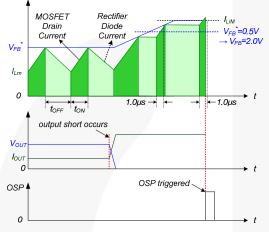


Figure 22. Output-Short Protection

4.4 Over-Voltage Protection (OVP): If the secondary-side feedback circuit malfunctions or a solder defect causes an opening in the feedback path, the current through the opto-coupler transistor becomes almost zero. Then VFB climbs up in a similar manner to the overload situation, forcing the preset maximum current to be supplied to the SMPS until the overload protection is triggered. Because more energy than required is provided to the output, the output voltage may exceed the rated voltage before the overload protection is triggered, resulting in the breakdown of the devices in the secondary side. To prevent this situation, an OVP circuit is employed. In general, the V<sub>CC</sub> is proportional to the output voltage and the FSL156MRBN uses V<sub>CC</sub> instead of directly monitoring the output voltage. If V<sub>CC</sub> exceeds 24.5V, an OVP circuit is triggered, resulting in the termination of the switching operation. To avoid undesired activation of OVP during normal operation, V<sub>CC</sub> should be designed to be below 24.5V.

**4.5 Thermal Shutdown (TSD)**: The SenseFET and the control IC on a die in one package makes it easier for the control IC to detect the over temperature of the SenseFET. If the temperature exceeds ~135°C, the thermal shutdown is triggered and stops operation. The FSL156MRBN operates in Auto-Restart Mode until the temperature decreases to around 75°C, when normal operation resumes.

**5.** Soft Burst-Mode Operation: To minimize power dissipation in Standby Mode, the FSL156MRBN enters Burst-Mode operation. As the load decreases, the feedback voltage decreases. As shown in Figure 23, the device automatically enters Burst Mode when the feedback voltage drops below  $V_{BURL}$  (350mV). At this point, switching stops and the output voltages start to drop at a rate dependent on standby current load. This causes the feedback voltage to rise. Once it passes  $V_{BURH}$  (500mV), switching resumes. The feedback voltage then falls and the process repeats. Burst Mode alternately enables and disables SenseFET switching, reducing switching loss in Standby Mode.

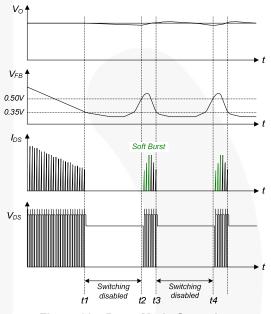
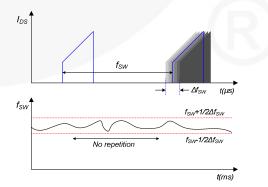


Figure 23. Burst-Mode Operation

**6. Random Frequency Fluctuation (RFF)**: Fluctuating switching frequency of an SMPS can reduce EMI by spreading the energy over a wide frequency range. The amount of EMI reduction is directly related to the switching frequency variation, which is limited internally. The switching frequency is determined randomly by external feedback voltage and an internal free-running oscillator at every switching instant. RFF effectively scatters EMI noise around typical switching frequency (67kHz) and can reduce the cost of the input filter included to meet the EMI requirements (e.g. EN55022).





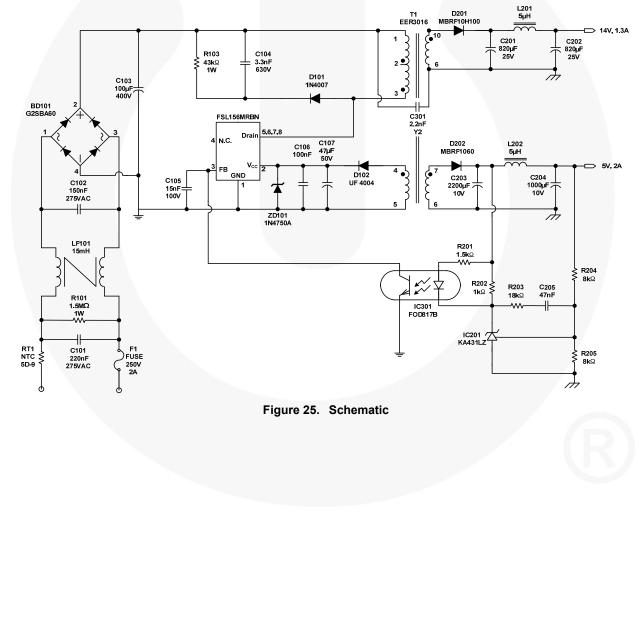
### **Typical Application Circuit**

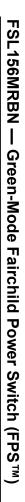
Application	Input Voltage	Rated Output	Rated Power
LCD Monitor Power Supply	85 ~ 265V <sub>AC</sub>	5.0V(2A) 14.0V(1.3A)	28.2W

#### **Key Design Notes**

- 1. The delay for overload protection is designed to be about 30ms with C105 (8.2nF). OLP time between 39ms (12nF) and 46ms (15nF) is recommended.
- The SMD-type capacitor (C106) must be placed as close as possible to the V<sub>CC</sub> pin to avoid malfunction by abrupt pulsating noises and to improve ESD and surge immunity. Capacitance between 100nF and 220nF is recommended.

#### Schematic





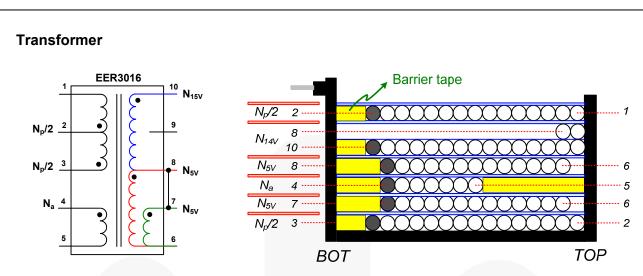


Figure 26. Schematic of Transformer

#### Winding Specification

		14/2	-		Barrier Tape		
	Pin (S $\rightarrow$ F)	Wire	Turns	Winding Method	ТОР	вот	Ts
N <sub>p</sub> /2	$3 \rightarrow 2$	0.25φ×1	22	Solenoid Winding		2.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					
N <sub>5V</sub>	$7 \rightarrow 6$	0.4φ×2 (TIW)	3	Solenoid Winding		3.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					
Na	$4 \rightarrow 5$	0.2φ×1	8	Solenoid Winding	4.0mm	3.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					
N <sub>5V</sub>	8 → 6	0.4φ×2 (TIW)	3	Solenoid Winding		3.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					
N <sub>14V</sub>	$10 \rightarrow 8$	0.4φ×2 (TIW)	5	Solenoid Winding		2.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					/
N <sub>p</sub> /2	$2 \rightarrow 1$	0.25φ×1	22	Solenoid Winding		2.0mm	1
Insulation: Polyeste	er Tape t = 0.025r	nm, 2 Layers					

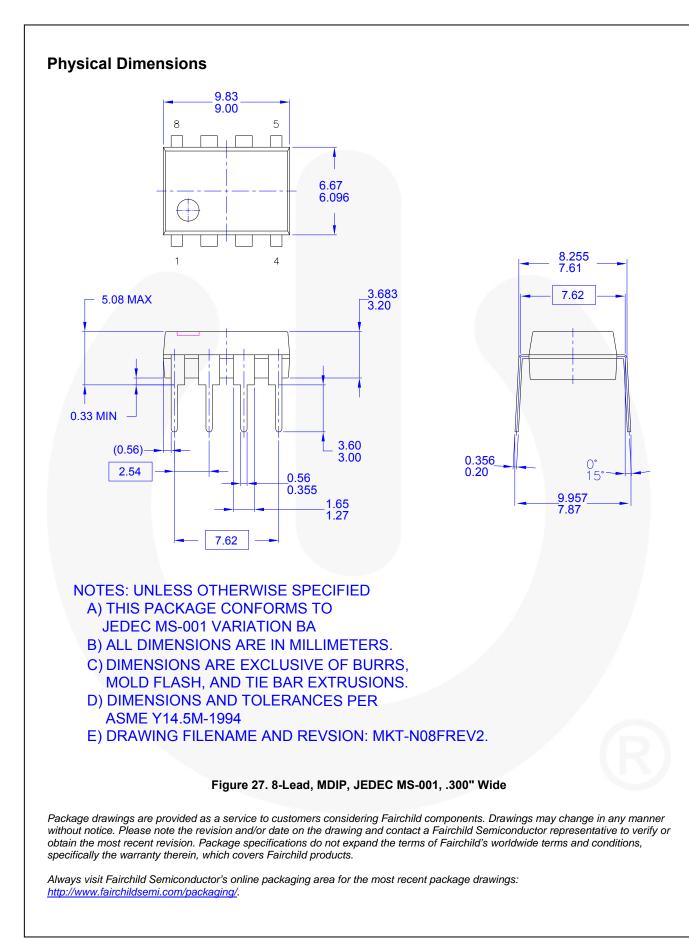
### **Electrical Characteristics**

	Pin	Specification	Remark
Inductance	1-3	826µH ±6%	67kHz, 1V
Leakage	1-3	15µH Maximum	Short all other pins

#### Core & Bobbin

- Core: EER3016 (Ae=109.7mm<sup>2</sup>)
- Bobbin: EER3016

Part #	Value	Note	Part #	Value	Note
	Fuse			Capacitor	
F101	250V 2A		C101	220nF / 275V	Box (Pilkor)
	NTC		C102	150nF/275V	Box (Pilkor)
NTC101	5D-9	DSC	C103	100µF / 400V	Electrolytic (SamYoung
	Resistor		C104	3.3nF/630V	Film (Sehwa)
R101	1.5MΩ, J	1W	C105	15nF / 100V	Film (Sehwa)
R103	43kΩ, J	1W	C106	100nF	SMD (2012)
R201	1.5kΩ, F	1/4W, 1%	C107	47µF / 50V	Electrolytic (SamYoung
R202	1.0kΩ, F	1/4W, 1%	C201	820µF / 25V	Electrolytic (SamYoung
R203	18kΩ, F	1/4W, 1%	C202	820µF / 25V	Electrolytic (SamYoung
R204	8kΩ, F	1/4W, 1%	C203	2200µF / 10V	Electrolytic (SamYoung
R205	8kΩ, F	1/4W, 1%	C204	1000µF / 16V	Electrolytic (SamYoung
			C205	47nF / 100V	Film (Sehwa)
			C301	2.2nF / Y2	Y-cap (Samhwa)
	IC		Inductor		
FPS	FSL156MRBN	Fairchild	LF101	20mH	Line filter 0.5Ø
IC201	KA431LZ	Fairchild	L201	5µH	5A Rating
IC301	FOD817B	Fairchild	L202	5µH	5A Rating
	Diode			Transformer	
D101	1N4007	Vishay	T101	826µH	
D102	UF4007	Vishay			
ZD101	1N4750	Vishay			
D201	MBRF10H100	Fairchild			
D202	MBRF1060	Fairchild			
BD101	G2SBA60	Vishay			



#### FAIRCHILD SEMICONDUCTOR TRADEMARKS The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks. The Power Franchise® 2Cool™ F-PFS™ PowerTrench<sup>®</sup> PowerXS™ AccuPower™ FRFET wer Global Power Resource<sup>34</sup> Programmable Active Droop™ AX-CAP™\* franchise GreenBridge™ OFET BitSiC™ TinyBoost™ Green FPS™ OS™ Build it Now™ TinyBuck™ Green FPS™ e-Series™ Quiet Series™ CorePLUS™ TinyCalc™ Gmax™ RapidConfigure™ **CorePOWER™** TinyLogic® GTOM CROSSVOLT™ **TINYOPTO™** IntelliMAX™ CTL™ Saving our world, 1mW/W/kW at a time™ TinyPower™ **ISOPLANAR**<sup>TM</sup> Current Transfer Logic™ TinyPWM™ SignalWise\* DEUXPEED Making Small Speakers Sound Louder SmartMax™ TinyWire™ Dual Cool™ and Better SMART START™ Tran SiC™ EcoSPARK® MegaBuck™ Solutions for Your Success™ TriFault Detect™ MICROCOUPLER™ EfficientMax™ SPM TRUECURRENT®\* MicroFET™ ESBC™ STEALTH" uSerDes™ R MicroPak™ F SuperFET N MicroPak2™ SuperSOT™-3 Fairchild® Miller Drive™ SuperSOT™-6 UHC Fairchild Semiconductor® Motion Max™ SuperSOT™-8 Ultra FRFET™ FACT Quiet Series™ Motion-SPM™ SupreMOS® UniFET™ FACT mWSaver™ **FAST®** SyncFET™ VCX™ OptoHiT™ Sync-Lock™ FastvCore™ VisualMax™ **OPTOLOGIC**® FETBench™ VoltagePlus™ **OPTOPLANAR®** FlashWriter®\* XS™ **FPS™** \* Trademarks of System General Corporation, used under license by Fairchild Semiconductor. DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

#### As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized fairbutors.

#### PRODUCT STATUS DEFINITIONS

Definition of Terms		
Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 161

SL156MRBN

I

Green-Mode Fairchild Power Switch (FPS<sup>™</sup>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: FSL156MRBN